# VS-HFA135NH40PbF

**Vishay Semiconductors** 

## HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 275 A



275 A

400 V

138 A at 100 °C

HALF-PAK (D-67)

Single diode

## FEATURES

- Very low Q<sub>rr</sub> and t<sub>rr</sub>
- Designed and qualified for industrial level
- Material categorization:
- For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### BENEFITS

- Reduced RFI and EMI
- Reduced snubbing

## DESCRIPTION

HEXFRED<sup>®</sup> diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dl/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V <sub>R</sub>		400	V
Continuous forward current	IF	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$	275	
		T <sub>C</sub> = 100 °C	138	A
Single pulse forward current	I <sub>FSM</sub>	Limited by junction temperature	900	
Non-repetitive avalanche energy	E <sub>AS</sub>	L = 100 $\mu H,$ duty cycle limited by maximum $T_{\rm J}$	1.4	mJ
Maximum power dissipation	P <sub>D</sub>	$T_{C} = 25 \ ^{\circ}C$	463	W
		T <sub>C</sub> = 100 °C	185	vv
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		400	-	-	
		I <sub>F</sub> = 135 A		-	1.06	1.65	v
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 270 A	See fig. 1	-	1.2	2.0	
		I <sub>F</sub> = 135 A, T <sub>J</sub> = 125 °C		-	0.96	1.58	
Maximum reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 125 °C, V <sub>R</sub> = 400 V	See fig. 2	-	-	3	mA
Junction capacitance	CT	V <sub>R</sub> = 200 V	See fig. 3	-	280	380	pF
Series inductance	L <sub>S</sub>	From top of terminal hole to mounting plane		-	6.0	-	nH

Revision: 01-Apr-14

1

Document Number: 94050

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



RoHS

COMPLIANT



**PRODUCT SUMMARY** 

I<sub>F</sub> (maximum)

 $V_{R}$ 

 $I_{F(DC)}$  at  $T_C$ 

Package

Circuit



Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	77	120	ns
		T <sub>J</sub> = 125 °C		-	280	440	
Peak recovery current See fig. 6	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 135 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	7.5	14	A
		T <sub>J</sub> = 125 °C		-	15	30	
Reverse recovery charge See fig. 7	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	150	780	nC
		T <sub>J</sub> = 125 °C		-	2800	6300	10
Peak rate of recovery current See fig. 8	dl <sub>(rec)M</sub> /dt	T <sub>J</sub> = 25 °C		-	350	-	A/µs
		T <sub>J</sub> = 125 °C		-	300	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction a temperature range	nd storage	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation See fig. 4	0.27	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	0.05		
Approvimate weight				30	g	
Approximate weight	Approximate weight			1.06	oz.	
Mounting torque	minimum			3 (26.5)		
Mounting torque	maximum			4 (35.4)	N⋅m	
Terminal torque	minimum			3.4 (30)	(lbf · in)	
	maximum			5 (44.2)		
Case style			HALF-PAK module			

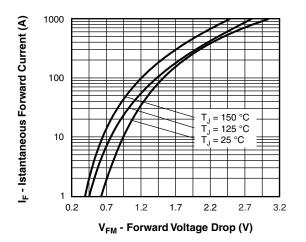


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

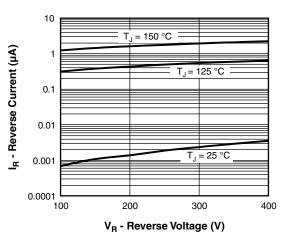


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



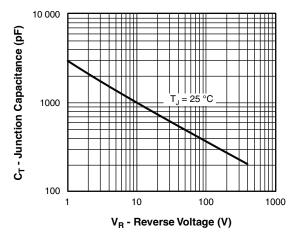


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

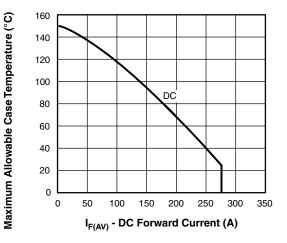


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current

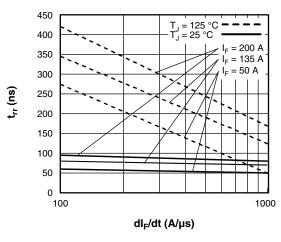


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

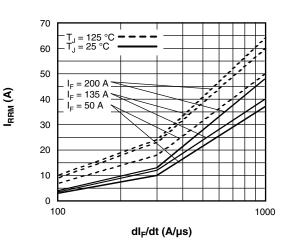


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

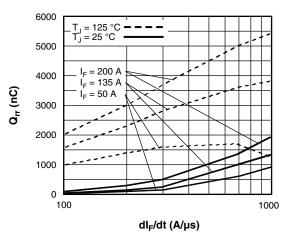


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

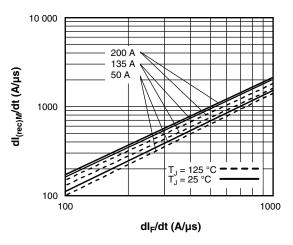


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

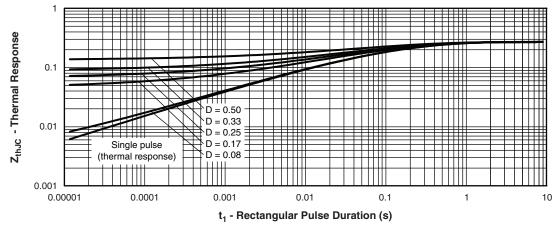
Revision: 01-Apr-14

3

Document Number: 94050

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

# VS-HFA135NH40PbF Vishay Semiconductors



www.vishay.com

Fig. 9 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

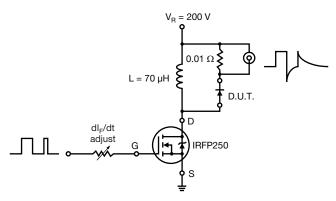


Fig. 10 - Reverse Recovery Parameter Test Circuit

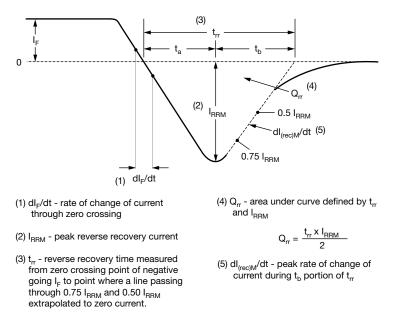


Fig. 11 - Reverse Recovery Waveform and Definitions

Revision: 01-Apr-14	4	Document Number: 94050
For technical questions within your region:	DiodesAmericas@vishay.com, DiodesAsia@vishay.c	com, <u>DiodesEurope@vishay.com</u>
	E WITHOUT NOTICE. THE PRODUCTS DESCRIBED CIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.co</u>	



## VS-HFA135NH40PbF

**Vishay Semiconductors** 

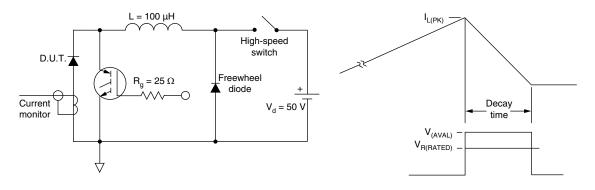
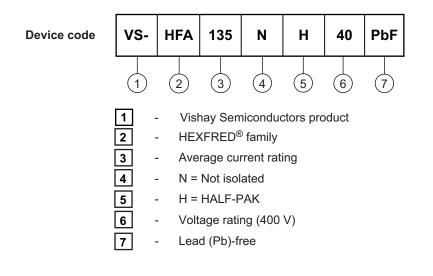


Fig. 12 - Avalanche Test Circuit and Waveforms

#### **ORDERING INFORMATION TABLE**



LINKS TO RELATED DOCUMENTS		
Dimensions	www.vishay.com/doc?95020	

Vishay Semiconductors

17.5 (0.69) 16.5 (0.65)



## **DIMENSIONS** in millimeters (inches)

SHAY





Vishay

# Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.